

## **Switchmode Dual Fast Recovery Power Rectifiers**

... Designed for use in switching power supplies. inverters and as free wheeling diodes. These state-of-the-art devices have the following features:

- \* Glass Passivated chip junctions

- \* Low Reverse Leakage Current
  \* Fast Switching for High Efficiency
  \* 150 °C Operating Junction Temperature
- \* Low Forward Voltage , High Current Capability
- \* Plastic Material used Carries Underwriters Laboratory Flammability Classification 94V-O

## **MAXIMUM RATINGS**

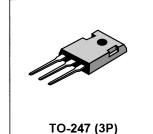
Characteristic	Symbol		Unit			
		30	40	50	60	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	300	400	500	600	٧
RMS Reverse Voltage	V <sub>R(RMS)</sub>	210	280	350	420	V
Average Rectifier Forward Current Per Leg T <sub>c</sub> =125°C Per Total Device	I <sub>F(AV)</sub>	15 30		A		
Peak Repetitive Forward Current ( Rate V <sub>R</sub> ,Square Wave,20kHz,T <sub>c</sub> =125°C )	I <sub>FM</sub>	30		Α		
Non-Repetitive Peak Surge Current (Surge applied at rate load conditions halfware,single phase,60Hz)	I <sub>FSM</sub>	200		А		
Operating and Storage Junction Temperature Range	T <sub>j</sub> , T <sub>stg</sub>		- 65 to	+ 150		°C

## **ELECTRICAL CHARACTERISTICS**

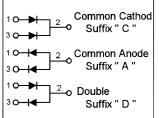
Characteristic	Symbol	F30D				Unit
		30	40	50	60	
Maximum Instantaneous Forward Voltage $(I_F=15 \text{ Amp}, T_C=25 ^{\circ}\text{C})$	V <sub>F</sub>	1.30			V	
Maximum Instantaneous Reverse Current ( Rated DC Voltage, $T_c = 25$ °C) ( Rated DC Voltage, $T_c = 125$ °C)	I <sub>R</sub>	10 700			uA	
Reverse Recovery Time ( $I_F = 0.5 \text{ A}, I_R = 1.0, I_{rr} = 0.25 \text{ A}$ )	T <sub>rr</sub>	250			ns	
Typical Junction Capacitance ( Reverse Voltage of 4 volts & f=1 MHz)	C <sub>P</sub>	1	50	1	120	pF

**FAST RECOVERY RECTIFIERS** 

**30 AMPERES** 300 -- 600 VOLTS



DIM	MILLMETERS		
Dilvi	MIN	MAX	
Α		16.2	
В	1.7	2.7	
С	5.0	6.0	
D		23.0	
Ε	14.8	15.2	
F	11.7	12.7	
G		4.5	
Н		2.5	
l		3.5	
J	1.1	1.4	
K	5.25	5.65	
L	19		
M	4.7	5.3	
N	2.8	3.2	
0	0.45	0.85	



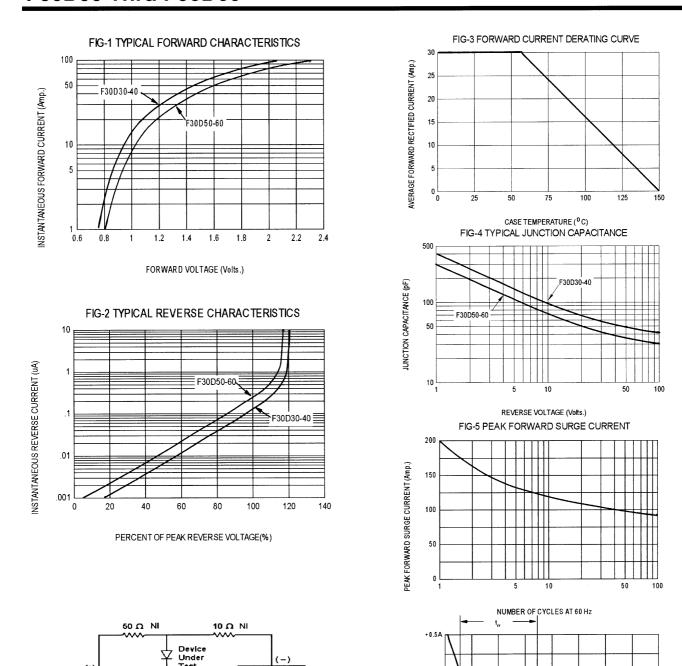
50 Vdc

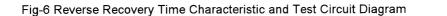
Approx

NI

Notes: 1. Rise Time = 7 ns max. Input Impedance =1 M  $\Omega$  , 22 pF 2. Rise Time = 10 ns max. Input Impedance = 50  $\Omega$ 

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-0.25A

Set time base for 50/100 ns/div

Pulse Generator ( Note 2)



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